

California State University Sacramento
Electrical and Computer Science Department

EEE 108L Lab - Section 05
Laboratory Experiment Number 6: Lab Report

MOS Device Characteristics

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Table of Contents

Abstract	3
 Part 1: Preliminary Calculations.....	3
STEP 1: Proving the Condition.....	3
STEP 2: Calculate I_D	3
STEP 3: Solve for V_{TH}	5
 Part 2: SPICE Simulation.....	5
STEP 4: Construct Circuit.....	5
STEP 5: Change circuit by removing R_D	6
STEP 6: (No Step 6 for this lab).....	6
STEP 7: Find Value for V_{TH}	8
 Part 3: Laboratory Experiment.....	9
STEP 8: Construct Circuit.....	9
STEP 9: Collect data to find the Value of V_{TH}	10
STEP 10: Record V_{GS} and Collect data for R_D	10
STEP 11: Connect the Bulk Terminal of the transistor to find the new V_{TH}	11
 CONCLUSION:	12
ITEM 1:	12
ITEM 2:	12
ITEM 3:	12
ITEM 4:	12
ITEM 5:	12
 ADDENDUM	

Abstract

For this laboratory experiment we will be exploring the characteristics of a MOS transistor. In this lab we are using the CD4007 MOS transistor.

Part 1: Preliminary Calculations

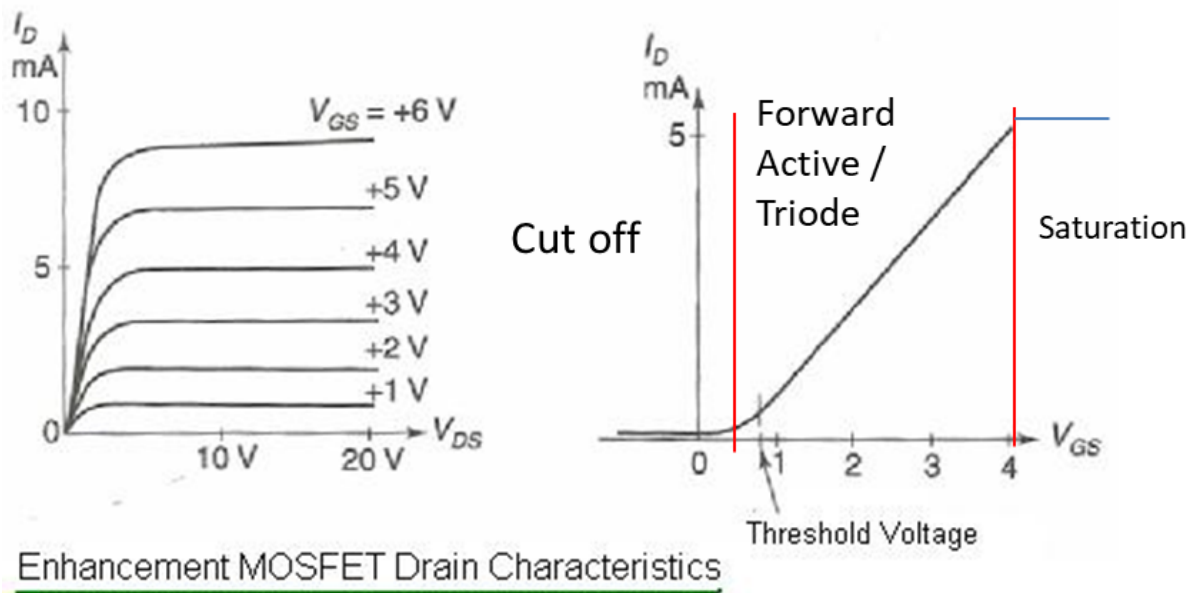
STEP 1:

$$V_{ds} > (V_{gs} - V_{th})$$

$$V_{ds} = (V_{gs} + V_{gd}) > (V_{gs} - V_{th})$$

$$V_{gd} > -V_{th}$$

$V_{gs} > V_{th}$, happens when the FET transistor is in the forward active region



STEP 2:

$$V_{ds} = V_{dd} - I_d R_d = V_{dd} - R (k (V_{gs} - V_{th})^2)$$

$$V_{dd} = 5V \text{ and } R = 4.7k\Omega$$

From Appendix A12.1 in Moodle

$$V_{th} = 1.6 \text{ V}, k = 8.2 \times 10^{-4}$$

$$I_d = 8.2 \times 10^{-4} (V_{gs} - 1.6 \text{ V})^2$$

$$V_{ds} = 5 - 4700 (8.2 \times 10^{-4} (V_{gs} - 1.6 \text{ V})^2)$$

When $V_{GS} = 1$,

$$I_d = (8.2 \times 10^{-4})(1 - 1.6)^2 = 2.95 \times 10^{-4}$$

$$V_{ds} = (5 - 4700)(2.95 \times 10^{-4}) = -1.362$$

When $V_{GS} = 2$,

$$I_d = (8.2 \times 10^{-4})(2 - 1.6)^2 = 1.3 \times 10^{-4}$$

$$V_{ds} = (5 - 4700)(1.3 \times 10^{-4}) = -0.610$$

When $V_{GS} = 4$,

$$I_d = (8.2 \times 10^{-4})(4 - 1.6)^2 = 4.72 \times 10^{-3}$$

$$V_{ds} = (5 - 4700)(4.72 \times 10^{-3}) = -22.160$$

VGS	I_d	V_{ds}	Region
1	2.95×10^{-4}	-1.362	Cut Off
2	1.3×10^{-4}	-0.610	Triode
4	4.72×10^{-3}	-22.160	Saturation

STEP 3:

Solve for V_{th} and the transconductance parameter

$$k = (\mu C_{ox} W) / 2L$$

$$I_d = k (V_{gs} - V_{th})^2$$

To find k and V_{th} , solve for 2 equations with 2 unknowns

$$35 \mu A = k (1.46 - V_{th})^2$$

$$430 \mu A = k (2.18 - V_{th})^2$$

Finding V_{th} ,

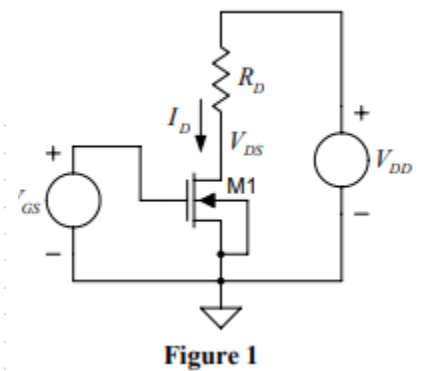
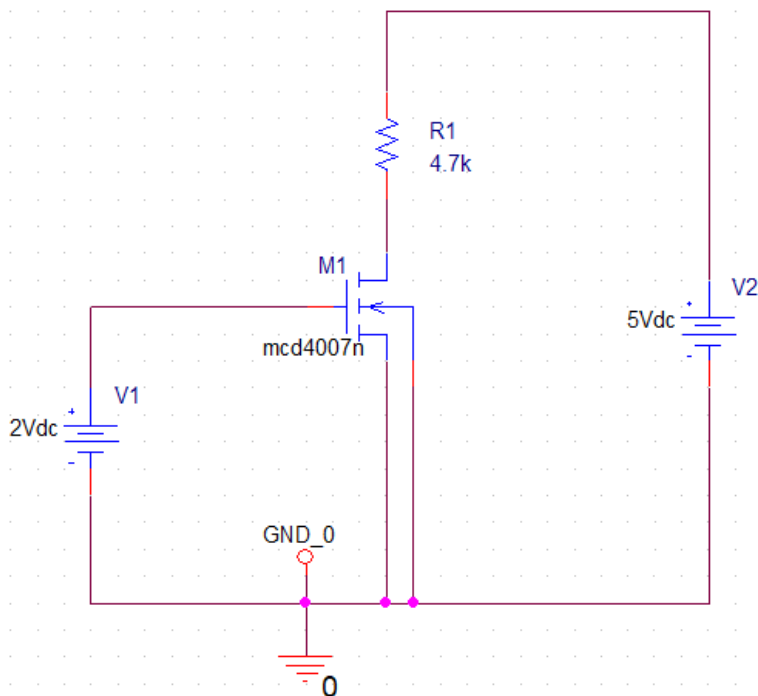
$$\text{Sqrt}(35/430) = (1.46 - V_{th}) / (2.18 - V_{th})$$

$$V_{th} = (1.46 - 0.2853(2.18)) / (1 - 0.2853)$$

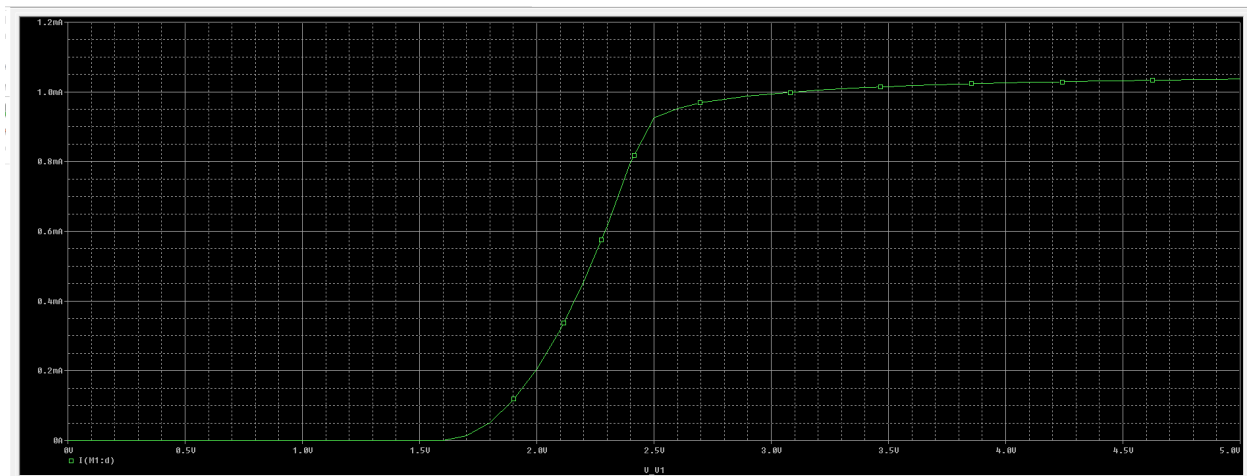
$$V_{th} = 1.173V$$

Part 2: Spice Calculations

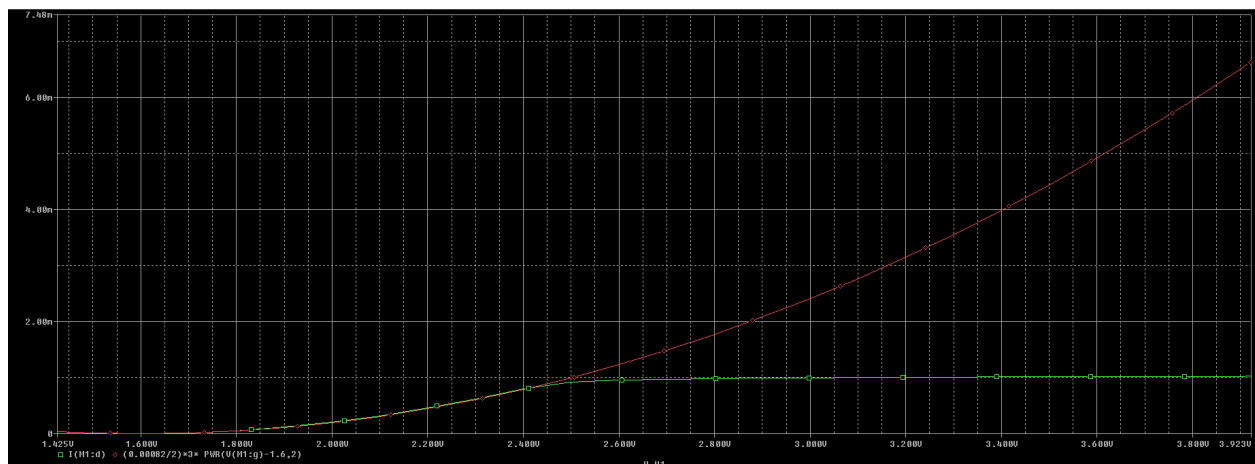
STEP 4: Construct circuit in figure 1 into Pspice.



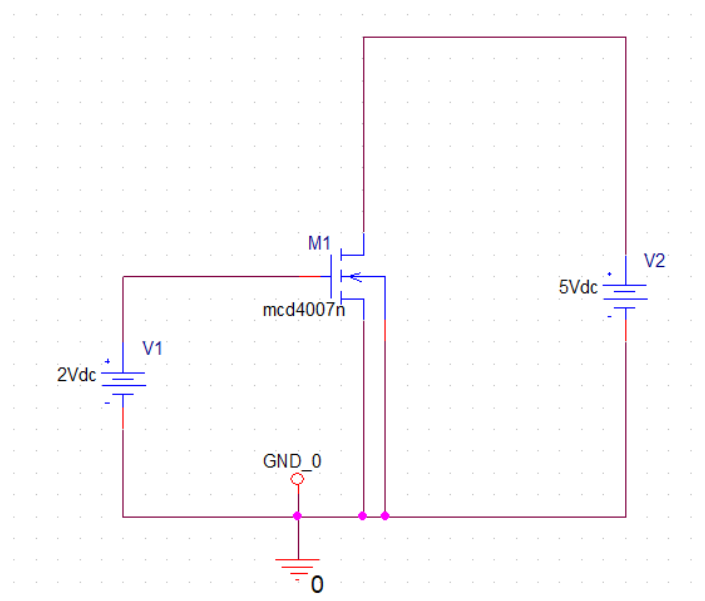
DC Sweep of Id



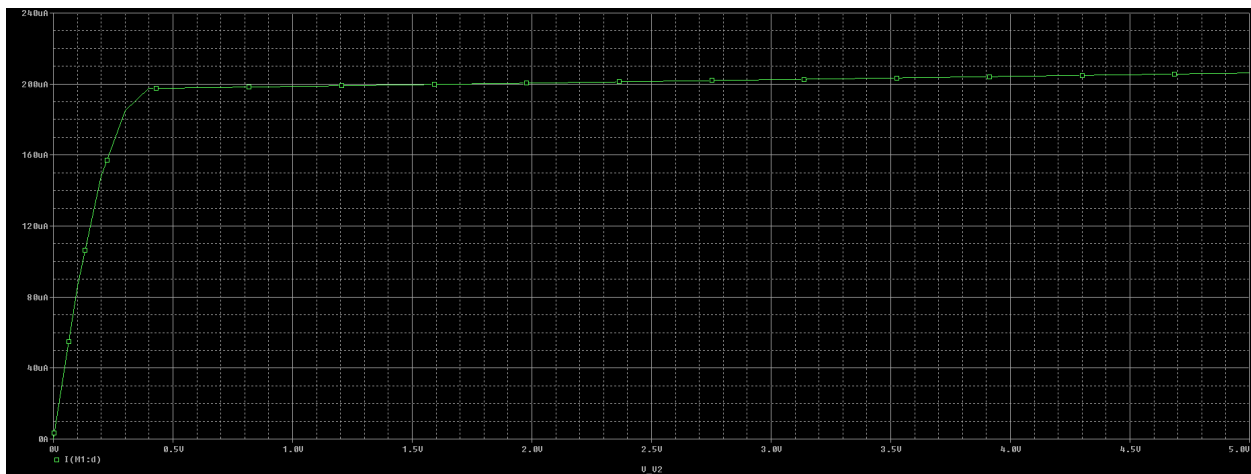
Current + Cox



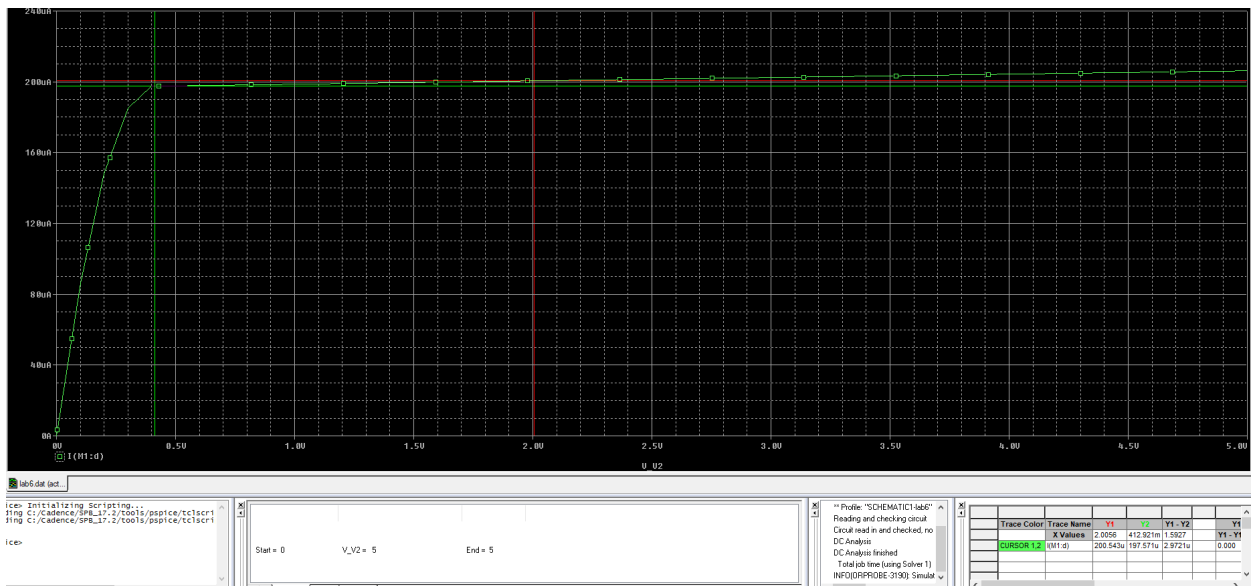
STEP 5: Remove the R



DC Sweep of Id

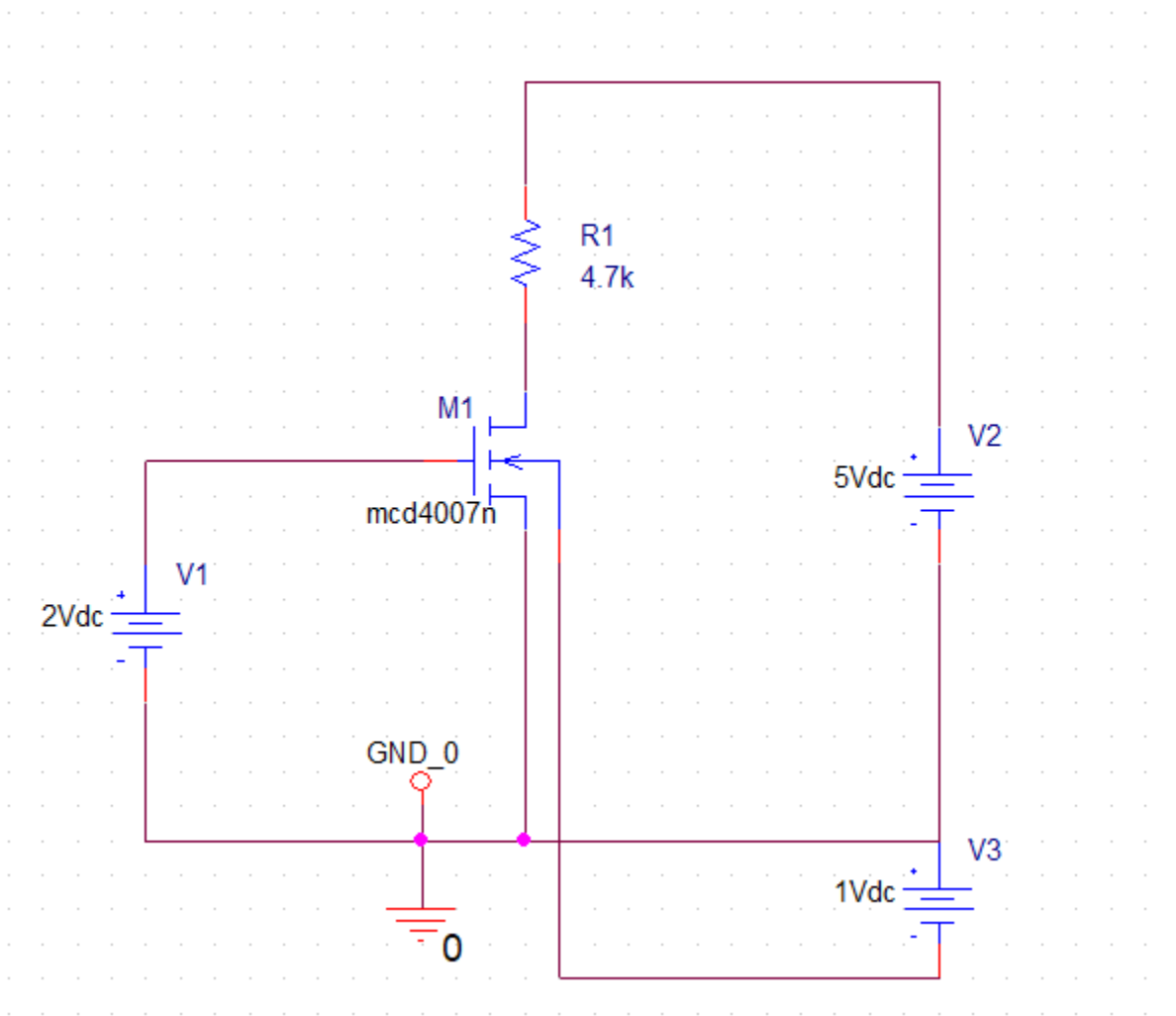


Forward Active Region (a little before the green cursor) and Saturation Region(red cursor)

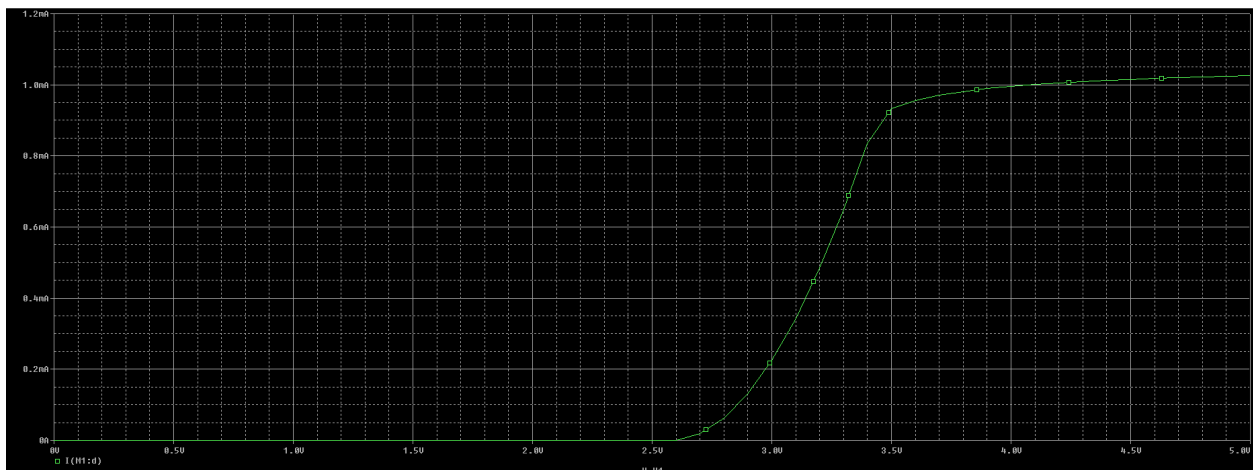


Trace Color	Trace Name	Y1	Y2	Y1 - Y2	Y1
	X Values	2.0056	412.921m	1.5927	Y1 - Y1
CURSOR 1,2	I(M1:d)	200.543u	197.571u	2.9721u	0.000

STEP 7: Construct Circuit



DC Sweep of VTH



Part 3: Laboratory Calculations

STEP 8: Construct Figure 1 Circuit

Vgs	Vds	Id	
0	4.96V	8.51×10^{-6}	
1	4.96V	8.51×10^{-6}	
1.5	4.96V	8.51×10^{-6}	
1.6	4.95V	1.06×10^{-5}	<-expected cut off
1.8	4.92V	1.70×10^{-5}	
2	4.81V	4.04×10^{-5}	
2.2	4.56V	9.36×10^{-5}	
2.4	4.21V	1.68×10^{-4}	
2.6	3.77V	2.62×10^{-4}	
2.8	3.23V	3.77×10^{-4}	
3	2.61V	5.09×10^{-4}	
3.2	1.93V	6.53×10^{-4}	
3.4	1.24V	8.00×10^{-4}	
3.6	840mV = 0.84V	8.85×10^{-4}	
3.8	695mV = 0.695V	9.16×10^{-4}	
4	617mV = 0.617V	9.34×10^{-4}	
5	443mV = 0.443V	9.70×10^{-4}	

STEP 9: Determine the value for V_{th} and K

$$I_d = 1.06 \times 10^{-5}$$

$$V_{gs} = 1.6$$

$$I_d = 4.04 \times 10^{-5}$$

$$V_{gs} = 2$$

$$(1.6 - V_{th}) / (2 - V_{th}) = \sqrt{1.06 \times 10^{-5} / 4.04 \times 10^{-5}}$$

$$(1.6 - V_{th}) = 0.512(2 - V_{th})$$

$$0.512 - 1 = 1.6 + (0.512)(2)$$

$$V_{th} = 2.624 / 0.488$$

$$V_{th} = 5.377$$

$$K = (1.06 \times 10^{-5}) / (1.6 - 5.377)^2$$

$$K = 7.43 \times 10^{-7}$$

Data from steps 10 and 11 were given from fellow team members and classmates.

STEP 10:

Step 10			
Vdd	Vds	Ids	
0	0.03	0.00097451	
1	0.152	0.000950588	
2	0.316	0.000918431	
3	0.54	0.00087451	
4	1.08	0.000768627	
5	2.01	0.000586275	
6	2.99	0.000394118	
7	3.94	0.000207843	

STEP 11:

Step 11				
Vdd=5		Vgs	Vds	Ids
		0	4.96	7.84314E-06
		1	4.96	7.84314E-06
		1.5	4.96	7.84314E-06
		1.6	4.96	7.84314E-06
		1.8	4.96	7.84314E-06
		2	4.96	7.84314E-06
		2.2	4.96	7.84314E-06
		2.4	4.96	7.84314E-06
		2.6	4.92	1.56863E-05
		2.8	4.73	5.29412E-05
		3	4.4	0.000117647
		3.2	3.93	0.000209804
		3.4	3.32	0.000329412
		3.6	2.59	0.000472549
		3.8	1.76	0.000635294
		4	1	0.000784314
		5	0.48	0.000886275

CONCLUSION:

ITEM 1: There is no difference between the values measured. The low = below 1.6 and the high = above 2.

ITEM 2: For the K values they were significantly different.

ITEM 3: For I_d values I see that they are fairly similar but with some differences in values. I think that is due to our circuit on the live board giving us strange values.

ITEM 4: For the values of V_{ds}/I_d in step 5 I found that it

ITEM 5: The value does change when comparing $V_{sb} = 0V$ to $V_{sb} = -1V$, as the value of the V_{th} increases slightly.